

High-Power Vertical GaN Electronic Devices Formed by Epitaxial Lift-Off

J Wang - 2018 - [curate.nd.edu](#)

... On the other hand, after lift-off, only the 1 μm highly doped n-GaN **lateral contact layer** and the 5 μm n-GaN buffer layer remains. This leads to a larger extrinsic series resistance. ...

☆ Save  Cite Cited by 1 Related articles All 3 versions 

Related searches

[lateral](#) [power](#) [mosfet](#) [trench](#) [gate](#)